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PTO/SB/08A (10-01)

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Substitute for form 1449A/PTO		Complete if Known			
		Application Number	09/910,537		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)		Filing Date	JULY 20, 2001		
		First Named Inventor	REID, J.		
		Art Unit	2822		
		Examiner Name	DUONG, K.		
Sheet	1	of	3	Attorney Docket Number	P21-US

U.S. PATENT DOCUMENTS					
Examiner Initials ¹	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code ² (if known)			
KBD	AA	US- 4,904,543	02-27-1990	SAKAKIMA et al.	
	AB	US- 5,262,000	11-16-1993	WELBOURNE et al.	
	AC	US- 5,439,754	08-08-1995	IWASAKI et al.	
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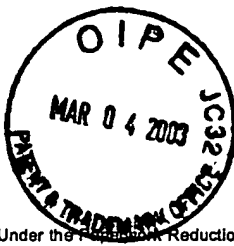
FOREIGN PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
		Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)				
KBD	BA	EP-1102329-A2	05-23-2001	MATSUSHITA et al.		

Examiner Signature	<i>John B. Dwyer</i>	Date Considered	11/28/2003
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		Group Art Unit	2822
		Examiner Name	DUONG, K.
		Attorney Docket Number	P21-US
Sheet	3	of	3

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS			
Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
KBD ↓	CL	LINDER et al., "Ternary Ta-Si-N Films for Sensors and Actuators", Sens. Actuators A, Phys. (Switzerland), Vol. A61 No. 1-3 (1997), pp. 387-391. ✓	
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	CN	NICOLET, M., "Reactively Sputtered Ternary Films of the Type TM-Si-N and their Properties (TM = Early Transition Metal)", Vacuum, Vol. 59 (2000), pp. 716-720. ✓	
	CO	OIZUMI et al., "Control of Crystalline Structure and Electrical Properties of TaSiN Thin Film Formed by Reactive RF-Sputtering", Jpn. J. Appl. Phys., Vol. 39 (2000), pp. 1291-1294. ✓	
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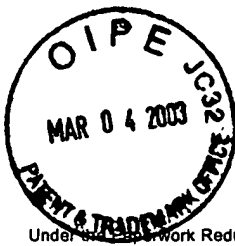
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KED	CA	BRIZOUAL et al., "Experimental Study of Ti-Si-N Films Obtained by Radio Frequency Magnetron Sputtering", Surface and Coatings Technology 116-119 (1999), pp. 922-926.	
	CB	CHERRY et al., "Stability of Conducting Amorphous Ru-Si-O Thin Films Under Oxygen Annealing", Microelectronic Engineering 55 (2001), pp. 403-408.	
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